

Nils Nordell

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

59
papers

1,868
citations

19
h-index

42
g-index

60
ext. papers

2,027
ext. citations

2.3
avg, IF

3.66
L-index

#	Paper	IF	Citations
59	Formation of precipitates in heavily boron doped 4H-SiC. <i>Applied Surface Science</i> , 2006 , 252, 5316-5320	6.7	10
58	Polytype homogeneity and doping distribution in homoepitaxial 4H SiC grown on nonplanar substrates. <i>Applied Physics Letters</i> , 2002 , 80, 1755-1757	3.4	6
57	Scanning capacitance microscopy investigations of SiC structures. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 209-211	4.3	11
56	Dissociation Energy of the Passivating Hydrogen-Aluminum Complex in 4H-SiC. <i>Materials Science Forum</i> , 2001 , 353-356, 427-430	0.4	7
55	Electric-field-assisted migration and accumulation of hydrogen in silicon carbide. <i>Physical Review B</i> , 2000 , 61, 7195-7198	3.3	11
54	Transient enhanced diffusion of implanted boron in 4H-silicon carbide. <i>Applied Physics Letters</i> , 2000 , 76, 1434-1436	3.4	44
53	Epitaxial Growth of 6SiC on Ion-Beam Synthesized 6SiC: Structural Characterization. <i>Materials Science Forum</i> , 2000 , 338-342, 309-312	0.4	3
52	Al/Si Ohmic Contacts to p-Type 4H-SiC for Power Devices. <i>Materials Science Forum</i> , 2000 , 338-342, 1009-1012	0.4	4
51	B implantation in 6HSiC: Lattice damage recovery and implant activation upon high-temperature annealing. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1040		5
50	Equilibrium crystal shapes for 6H AND 4H SiC grown on non-planar substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 130-134	3.1	8
49	Epitaxial growth of SiC in a new multi-wafer VPE reactor. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 143-146	3.1	5
48	Investigation of surface recombination and carrier lifetime in 4H/6H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 239-243	3.1	19
47	Diffusion of light elements in 4H and 6H SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 275-280	3.1	13
46	Study of the electrical, thermal and chemical properties of Pd ohmic contacts to p-type 4H-SiC: dependence on annealing conditions. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 291-295	3.1	8
45	Hall effect investigations of 4H SiC epitaxial layers grown on semi-insulating and conducting substrates. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 389-394	3.1	17
44	Temperature stable Pd ohmic contacts to p-type 4H-SiC formed at low temperatures. <i>IEEE Transactions on Electron Devices</i> , 1999 , 46, 605-611	2.9	24
43	Surface roughening in ion implanted 4H-silicon carbide. <i>Journal of Electronic Materials</i> , 1999 , 28, 214-218	1.9	86

42	Boron implantation and epitaxial regrowth studies of 6H SiC. <i>Journal of Electronic Materials</i> , 1998 , 27, 833-837	1.9	4
41	Study of avalanche breakdown and impact ionization in 4H silicon carbide. <i>Journal of Electronic Materials</i> , 1998 , 27, 335-341	1.9	81
40	Electrical Activation of B Implant in 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 705-708	0.4	
39	Comparison of SiO ₂ and AlN as Gate Dielectric for SiC MOS Structures. <i>Materials Science Forum</i> , 1998 , 264-268, 877-880	0.4	9
38	6H-SiC Crystallinity Behaviour upon B Implantation Studied by Raman Scattering. <i>Materials Science Forum</i> , 1998 , 264-268, 741-744	0.4	
37	Transmission Electron Microscopy Investigation of Defects in B-Implanted 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 413-416	0.4	10
36	Ground States of the Ionized Isoelectronic Ti Acceptor in SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 537-540	0.4	4
35	AFM Study of In Situ Etching of 4H and 6H SiC Substrates. <i>Materials Science Forum</i> , 1998 , 264-268, 363-366		6
34	Ionization Rates and Critical Fields in 4H SiC Junction Devices. <i>Materials Science Forum</i> , 1998 , 264-268, 513-516	0.4	24
33	Growth of 4H and 6H SiC Trenches and Around Stripe Mesas. <i>Materials Science Forum</i> , 1998 , 264-268, 131-134	0.4	3
32	Thermostable Ohmic Contacts on p-Type SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 787-790	0.4	14
31	SiC Surface Engineering for High Voltage JFET Applications. <i>Materials Science Forum</i> , 1998 , 264-268, 1081-1084	0.4	
30	Deuterium Incorporation in Acceptor Doped Epitaxial Layers of 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 761-764	0.4	3
29	Incorporation of the D-Center in SiC Controlled either by Coimplantation of Si/B and C/B or by Site-Competition Epitaxy. <i>Materials Science Forum</i> , 1998 , 264-268, 681-684	0.4	12
28	Temperature dependence of avalanche breakdown for epitaxial diodes in 4H silicon carbide. <i>Applied Physics Letters</i> , 1998 , 73, 1850-1852	3.4	30
27	Electrically active point defects in n-type 4H SiC. <i>Journal of Applied Physics</i> , 1998 , 84, 1354-1357	2.5	64
26	Homoepitaxy of 6H and 4H SiC on nonplanar substrates. <i>Applied Physics Letters</i> , 1998 , 72, 197-199	3.4	7
25	Observation of near-surface electrically active defects in n-type 6H SiC. <i>Journal of Applied Physics</i> , 1998 , 83, 3649-3651	2.5	1

24	Electrical properties of the titanium acceptor in silicon carbide. <i>Physical Review B</i> , 1997 , 55, 13618-13624.	3.3	59
23	Influence of growth conditions on electrical characteristics of AlN on SiC. <i>Applied Physics Letters</i> , 1997 , 70, 3549-3551	3.4	29
22	Deep level defects in electron-irradiated 4H SiC epitaxial layers. <i>Journal of Applied Physics</i> , 1997 , 81, 6155-6159.	3.4	24
21	Investigation of aluminum nitride grown by metalorganic chemical-vapor deposition on silicon carbide. <i>Journal of Applied Physics</i> , 1997 , 82, 2990-2995	2.5	55
20	High-voltage operation of field-effect transistors in silicon carbide. <i>IEEE Electron Device Letters</i> , 1997 , 18, 521-522	4.4	6
19	Ionization rates and critical fields in 4H silicon carbide. <i>Applied Physics Letters</i> , 1997 , 71, 90-92	3.4	319
18	Hydrogen incorporation in epitaxial layers of 4H- and 6H-silicon carbide grown by vapor phase epitaxy. <i>Diamond and Related Materials</i> , 1997 , 6, 1293-1296	3.5	11
17	Characterization of electrically active deep level defects in 4H and 6H SiC. <i>Diamond and Related Materials</i> , 1997 , 6, 1388-1391	3.5	21
16	Control of Al and B doping transients in 6H and 4H SiC grown by vapor phase epitaxy. <i>Journal of Electronic Materials</i> , 1997 , 26, 187-192	1.9	19
15	Capacitance transient studies of electron irradiated 4H-SiC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 336-339	3.1	13
14	Deep Defect Centers in Silicon Carbide Monitored with Deep Level Transient Spectroscopy. <i>Physica Status Solidi A</i> , 1997 , 162, 199-225		330
13	Design and Performance of a New Reactor for Vapor Phase Epitaxy of 3C, 6H, and 4H SiC. <i>Journal of the Electrochemical Society</i> , 1996 , 143, 2910-2919	3.9	34
12	Theory and Realization of a Two - Layer Hall Effect Measurement Concept for Characterization of Epitaxial and Implanted Layers of SiC. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 423, 661		7
11	Influence of H ₂ Addition and Growth Temperature on CVD of SiC Using Hexamethyldisilane and Ar. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 565-571	3.9	21
10	Growth of SiC using hexamethyldisilane in a hydrogen-poor ambient. <i>Applied Physics Letters</i> , 1994 , 64, 1647-1649	3.4	23
9	Improved InP regrowth properties in metalorganic vapor phase epitaxy by addition of CCl ₄ . <i>Applied Physics Letters</i> , 1992 , 61, 22-24	3.4	21
8	Design and Performance of a New Reactor for Metal Organic Vapor Phase Epitaxial Growth of Extremely Uniform Layers. <i>Journal of the Electrochemical Society</i> , 1992 , 139, 583-590	3.9	3
7	Influence of MOVPE growth conditions and CCl ₄ addition on InP crystal shapes. <i>Journal of Crystal Growth</i> , 1992 , 125, 597-611	1.6	15

6	Growth and performance of AlGaAs/GaAs heterostructure bipolar transistors. <i>Journal of Crystal Growth</i> , 1991 , 107, 909-914	1.6	5
5	MOVPE growth of InP around reactive ion etched mesas. <i>Journal of Crystal Growth</i> , 1991 , 114, 92-98	1.6	18
4	MOVPE regrowth of semi-insulating InP around reactive ion etched laser mesas. <i>Electronics Letters</i> , 1991 , 27, 926-927	1.1	10
3	Diffusion of Zn and Mg in AlGaAs/GaAs structures grown by metalorganic vapor-phase epitaxy. <i>Journal of Applied Physics</i> , 1990 , 67, 778-786	2.5	29
2	Low-power optical bistability in a thermally stable AlGaAs Fabon. <i>Applied Physics Letters</i> , 1989 , 54, 2290-2292	3.4	12
1	Bistable switching in nonlinear Al _{0.06} Ga _{0.94} As Fabons. <i>Applied Physics Letters</i> , 1988 , 53, 1785-1787	3.4	13